# **High Voltage Power Transistors**

# **DPAK for Surface Mount Applications**

Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular MJE340 and MJE350
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating		Symbol	Max	Unit
Collector-Emitter Voltage		V <sub>CEO</sub>	300	Vdc
Collector-Base Voltage		V <sub>CB</sub>	300	Vdc
Emitter-Base Voltage		V <sub>EB</sub>	3	Vdc
Collector Current – Contin	iuous	Ic	0.5	Adc
Collector Current – Peak		I <sub>CM</sub>	0.75	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C		P <sub>D</sub>	15 0.12	W W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C Derate above 25°C		P <sub>D</sub>	1.56 0.012	W W/°C
Operating and Storage Junction Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
ESD – Human Body Model MJD340 (NPN) MJD350 (PNP)		HBM	3B 2	V
ESD – Machine Model	MJD340 (NPN) MJD350 (PNP)	MM	M4 M4	V

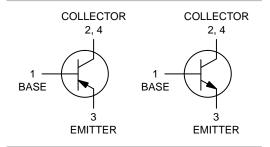
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### ON Semiconductor®

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# SILICON POWER TRANSISTORS 0.5 AMPERE 300 VOLTS, 15 WATTS





DPAK CASE 369C STYLE 1

#### **MARKING DIAGRAM**



A = Assembly Location

Y = Year

WW = Work Week

J3x0 = Device Code

x= 4 or 5

G = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	8.33	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	80	°C/W
Leading Temperature for Soldering Purpose	TL	260	°C

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) (I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	300	-	V
Collector Cutoff Current (V <sub>CB</sub> = 300 V, I <sub>E</sub> = 0)	I <sub>CEO</sub>	-	0.1	mA
Emitter Cutoff Current (V <sub>BE</sub> = 3 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.1	mA
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	30	240	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA)	V <sub>CE(sat)</sub>	-	1	V
Base–Emitter On Voltage (I <sub>C</sub> = 1 A, V <sub>CE</sub> = 10 V)	V <sub>BE(on)</sub>	-	1.5	V
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 V, f = 10 MHz)	f <sub>T</sub>	10	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

#### **TYPICAL CHARACTERISTICS**

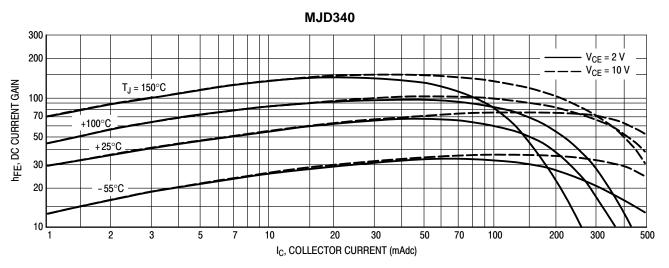


Figure 1. DC Current Gain

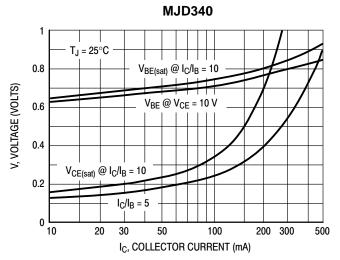
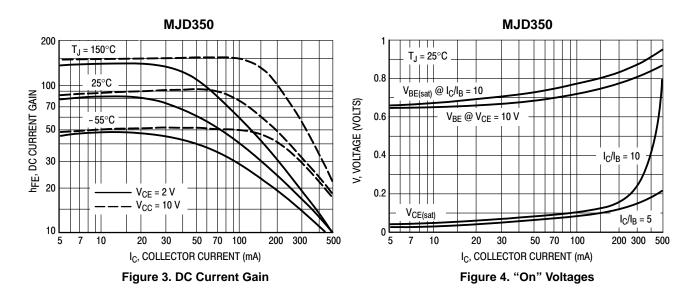


Figure 2. "On" Voltages



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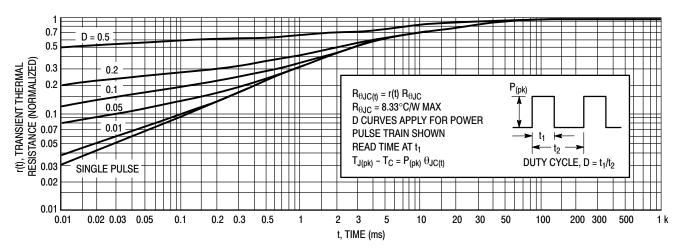


Figure 5. Thermal Response

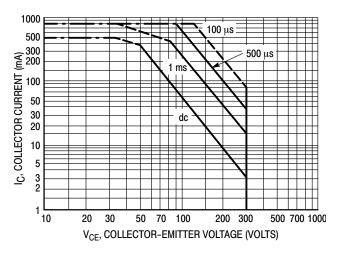


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

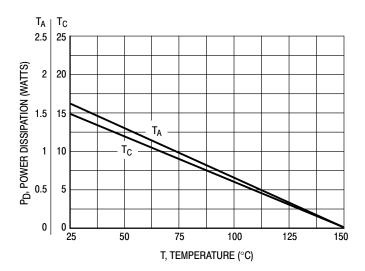


Figure 7. Power Derating

#### **ORDERING INFORMATION**

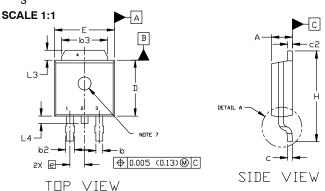
Device	Package	Shipping <sup>†</sup>
MJD340G	DPAK (Pb-Free)	75 Units / Rail
MJD340RLG	DPAK (Pb-Free)	1,800 / Tape & Reel
MJD340T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NJVMJD340T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
MJD350G	DPAK (Pb-Free)	75 Units / Rail
MJD350T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NJVMJD350T4G	DPAK (Pb-Free)	2,500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





**DATE 31 MAY 2023** 



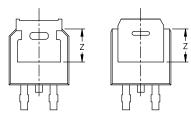


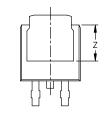
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. L3, AND Z.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
  GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  DIMENSIONS D AND E ARE DETERMINED AT THE
  OUTERMOST EXTREMES OF THE PLASTIC BODY.
  DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
  DETININAL MOLD ESCALUES.

- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
MIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
C	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020	0.020 BSC 0.51		BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

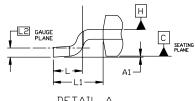




BOTTOM VIEW

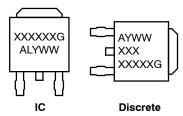
BOTTOM VIEW ALTERNATE CONSTRUCTIONS

5.80 [0.228] 6.20 [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17 [0.243]



DETAIL A ROTATED 90° CW

**GENERIC MARKING DIAGRAM\*** 



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

\*This information is generic. Please refer to

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

3 FMITTER

4. COLLECTOR

s

3 GATE

RECOMMENDED MOUNTING FOOTPRINT\*

STYLE 1: STYLE 2: PIN 1. BASE PIN 1. GATE 2. COLLECTOR 2. DRAIL 3. EMITTER 3. SOUF 4. COLLECTOR 4. DRAIL	N 2. CATHODE RCE 3. ANODE	3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
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STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE

4. CATHODE

device data sheet for actual part marking. PIN 1. CATHODE 2. ANODE 3. CATHODE Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may 3 RESISTOR ADJUST not follow the Generic Marking. 4. ANODE

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

4. CATHODE

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